

SILICON TRANSISTOR ARRAY

μ PA1437

PNP SILICON POWER TRANSISTOR ARRAY LOW SPEED SWITCHING USE (DARLINGTON TRANSISTOR) INDUSTRIAL USE

DESCRIPTION

The μ PA1437 is PNP silicon epitaxial Darlington Power Transistor Array that built in 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- Easy mount by 0.1 inch of terminal interval.
- · High hee for Darlington Transistor.

ORDERING INFORMATION

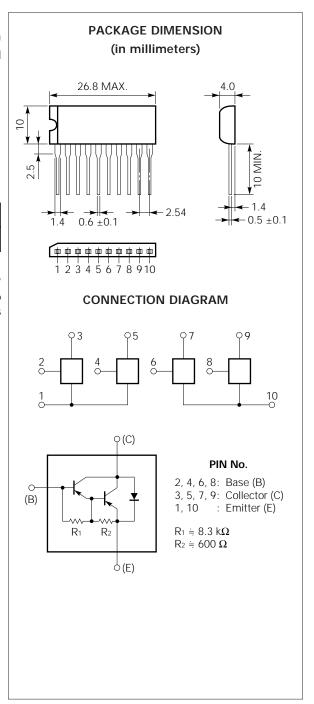
Part Number	Package	Quality Grade		
μPA1437H	10 Pin SIP	Standard		

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Vсво	-100	V
V_{CEO}	-100	V
V_{EBO}	- 7	V
Ic(DC)	∓3	A/unit
Ic(pulse)*	∓ 6	A/unit
B(DC)	-0.3	A/unit
P _{T1} **	3.5	W
P _{T2} ***	28	W
Tj	150	,C
Tstg -55	to +150) .C
	VCEO VEBO Ic(DC) Ic(pulse)* IB(DC) PT1** PT2*** Tj	Vceo −100 Vebo −7 Ic(pc) ∓3 Ic(pulse)* ∓6 IB(pc) −0.3 PT1** 3.5 PT2*** 28 Tj 150

- * PW \leq 300 μ s, Duty Cycle \leq 10 %
- ** 4 Circuits, Ta = 25 °C
- *** 4 Circuits, Tc = 25 °C



The information in this document is subject to change without notice.

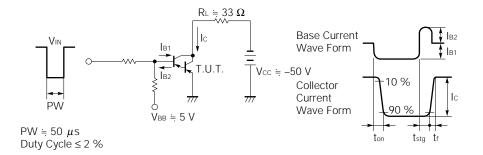


ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector to Emitter Sustaining Voltage	VCEO(SUS)	-100			V	Ic = -1.5 A, I _B = -1.5 mA, L = 1 mH
Collector Leakage Current	Ісво			-10	μΑ	Vcb = -100 V, IE = 0
Emitter Leakage Current	Ієво			-1	mA	V _{EB} = -5 V, I _C = 0
DC Current Gain	h _{FE1} *	1000			_	Vce = -2 V, Ic = -0.5 A
DC Current Gain	h _{FE2} *	2000		20000	_	Vce = -2 V, Ic = -1.5 A
Collector Saturation Voltage	VcE(sat) *		-0.9	-1.2	V	Ic = -1.5 A, $IB = -1.5 mA$
Base Saturation Voltage	V _{BE(sat)} *		-1.5	-2	V	Ic = -1.5 A, I _B = -1.5 mA
Turn On Time	ton		1		μs	Ic = -1.5 A
Storage Time	tstg		3		μs	$\begin{array}{l} I_{B1} = -I_{B2} = -1.5 \text{ mA} \\ V_{CC} \stackrel{.}{=} 50 \text{ V}, \text{ RL} \stackrel{.}{=} 33 \Omega \\ \text{See test circuit} \end{array}$
Fall Time	tr		1		μs	

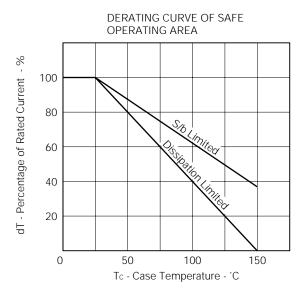
^{*} PW \leq 350 μ s, Duty Cycle \leq 2 % / pulsed

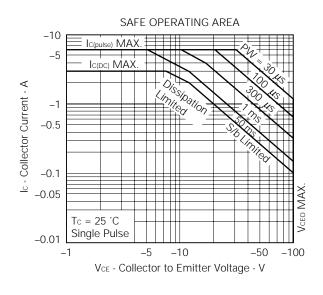
SWITCHING TIME TEST CIRCUIT



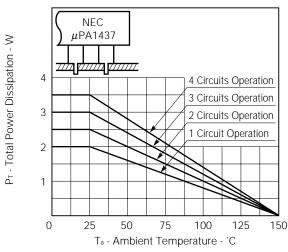


TYPICAL CHARACTERISTICS (Ta = 25 °C)

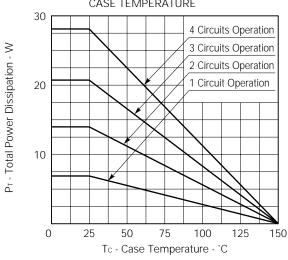




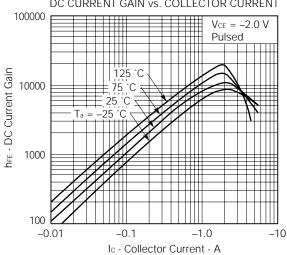




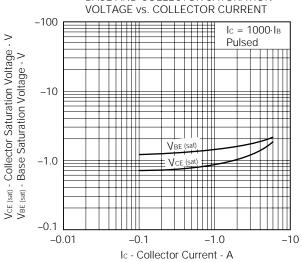




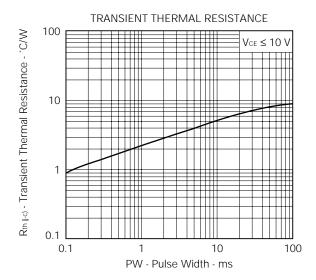
DC CURRENT GAIN vs. COLLECTOR CURRENT

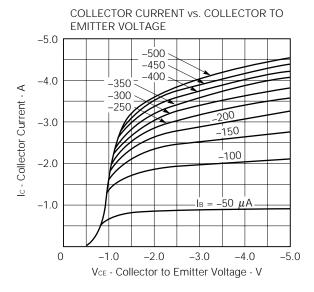


BASE AND COLLECTOR SATURATION











REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

5

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